RO	HM	PRODUCTS		ТҮРЕ		PAGE			
		Silicon monolithic IC		BU26507GU	1/4				
 Structure 	e	Silicon Monolithic Integrated Circuit							
 Product 	Name	5x6 dot mat	trix LED driver	for portable device					
● Туре		BU2650	6507GUL						
● Feature:	S	driven seque Automatic SI	entially	d 6-channel current dri 8 directions)	vers with 1/5 TD	MA timing			
 Absolute 	e Maximum R	atings (Ta=25 °	C)			_			
		meter	Symbol	Limits	Unit	4			
	laximum volta		VMAX	7	V	_			
	ower Dissipat		Pd	790	mW	_			
	torage Tempe	perature Range	Topr Tstg	-40 ~ +85 -55 ~ +125	ິ ສ	_			
note1)	<u>-</u>	ation deleting is 7.9r							
	P	(VBAT≥VIO, 1 ?arameter	a=-40~85°C) Symbol	Limits	Unit				
	BAT input voltag		VBAT	2.7 ~ 5.5	V				
	NSW input volt	age	VINSW	2.7 ~ 5.5	V				
VIO pin voltage			VIO	1.65 ~ 3.3	V				
Status of thi The Japane A customer	is document se version of this do may use this transla	d to protect itself a boument is the formal sp ation version only for a n anslation version of this	pecification. eference to help read	ing the formal version.					
 The product de office-automati Should you int would directly controllers and ROHM assume 	provide adequate of escribed in this sp on equipment, con end to use this pr endanger human I other safety devic es no responsibilit	nmunications devices, oduct with equipment ife (such as medical i es), please be sure to	d to be used with o electrical appliance t or devices which a nstruments, transpo consult with our sa circuits described h	rdinary electronic equipment or is, and electronic toys). equire an extremely high level irtation equipment, aerospace i es representative in advance. erein, conveys no license unde	of reliability and the r machinery, nuclear-rea	nalfunction of which ctor controllers, fuel			
DESIGN Hiroxuki Tanioana	CHECK K.Kovniya	APPROVAL LKomiya)ate : May/10/2	011 SPECIFICATION No	.: TSZ02201-BU	26507GUL-1-2			
10migawa May 10/2011	May/10/11	К. Котіча (4. Котіча (4. Котіча)	REV. A	RO	HM Co.,L	td.			

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BU26507GUL

TYPE

Deservator	Symbol	Limit					
Parameter		Min.	Тур.	Max.	Unit	Condition	
[Circuit Current]							
VBAT Circuit current 1	IBAT1	-	0	3.0	μA	RESETB=0V, VIO=0V	
VBAT Circuit current 2	IBAT2	-	0.5	5.0	μA	RESETB=0V, VIO=1.8V	
VBAT Circuit current 3 [UVLO]	IBAT3	-	0.8	1.4	mA	When LED1-6 are active with default settings.	
UVLO Threshold	VUVLO	-	2.1	2.5	v	VBAT falling	
UVLO Hysteresis	VHYUVLO	50			mV		
[LED Driver] (LED1-6)	1110120						
	ILEDMax1	-	20.00	-	mA	LED1-6 ,ISET=100kΩ	
Maximum output current	ILEDMax2	-	42.50	-	mA	LED1-6 ,ISET=47kΩ	
Output current	ILED	-7.0%	10.67	+7.0%	mA	I=10.67mA setting, VLED=1V,ISET=100 kΩ	
LED current Matching	ILEDMT	-	-	5	%	ILEDMT= (ILEDMax-ILEDMin)/(ILEDMax+ILEDMin) I=10.67mA setting, VLED=1V	
Driver pin voltage range	VLED	0.2	-	VBAT - 1.4	v	ISET=100 kΩ	
LED OFF Leak current [PMOS switch]	ILKLED	-	-	1.0	μA		
Leak current at OFF	ILEAKP	-	-	1.0	μA		
Resistor at ON	RonP	-	1.0	-	Ω	Isw=60mA, VINSW=4.5V	
OSC frequency	fosc	0.96	1.2	1.44	MHz		
CE, SYNC, IFMODE]							
_ level input voltage	VIL1	-0.3	-	0.25 x VIO	v		
H level input voltage	VIH1	0.75 x VIO	-	VIO +0.3	v		
L level input current	IIL1	-	0	1	μA		
H level input current	IIH1	-	0	1	μA		
[SDA, SCL]							
L level input voltage	VIL2	-0.3	-	0.25 x VIO	V		
H level input voltage	VIH2	0.75 x VIO	-	VIO +0.3	V		
Input hysteresis	Vhys	0.05 x VIO	-	-	V		
L level output voltage (for SDA pin)	VOL2	0	-	0.3	v	IOL=3mA	
Input current	lin1	-3	-	3	μA	Input voltage = from (0.1 x VIO) to (0.9 x VIO)	
[RESETB]		-			P** `		
L level input voltage	VIL3	-0.3	-	0.25 x VIO	v		
H level input voltage	VIH3	0.75 x VIO	-	VIO +0.3	v		
Input current	lin2	-	0	1	μA	Input voltage = from (0.1 x ViO) to (0.9 x VIO)	
[CLKIO(OUTPUT)]				I			
L level output voltage	VOL1	-	-	0.4	v	IOL=2mA	
H level output voltage	VOL1 VOH1	0.75 x VIO	-	-	 	IOH=-2mA	
[CLKIO(INPUT)]					-	.I	
L level input voltage	\ <i>1</i> 11 A	-0.3		0.25 x			
	VIL4	-0.3 0.75 x	-	VIO VIO			
H level input voltage	VIH4	VIO	-	+0.3	V		
Input current	lin3	-	3.6	10	μΑ	input voltage=1.8V	

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TYPE





BU26507GUL

- Cautions on use
- (1) Absolute Maximum Ratings

An excess in the absolute maximum ratings, such as supply voltage, temperature range of operating conditions, etc., can break down devices, thus making impossible to identify breaking mode such as a short circuit or an open circuit. If any special mode exceeding the absolute maximum ratings is assumed, consideration should be given to take physical safety measures including the use of fuses, etc.

TYPE

(2) Power supply and ground line

Design PCB pattern to provide low impedance for the wiring between the power supply and the ground lines. Pay attention to the interference by common impedance of layout pattern when there are plural power supplies and ground lines. Especially, when there are ground pattern for small signal and ground pattern for large current included the external circuits, please separate each ground pattern. Furthermore, for all power supply pins to ICs, mount a capacitor between the power supply and the ground pin. At the same time, in order to use a capacitor, thoroughly check to be sure the characteristics of the capacitor to be used present no problem including the occurrence of capacity dropout at a low temperature, thus determining the constant.

(3) Ground voltage

Make setting of the potential of the ground pin so that it will be maintained at the minimum in any operating state. Furthermore, check to be sure no pins are at a potential lower than the ground voltage including an actual electric transient.

- (4) Short circuit between pins and erroneous mounting In order to mount ICs on a set PCB, pay thorough attention to the direction and offset of the ICs. Erroneous mounting can break down the ICs. Furthermore, if a short circuit occurs due to foreign matters entering between pins or between the pin and the power supply or the ground pin, the ICs can break down.
- (5) Operation in strong electromagnetic field
- Be noted that using ICs in the strong electromagnetic field can malfunction them.

(6) Input pins

In terms of the construction of IC, parasitic elements are inevitably formed in relation to potential. The operation of the parasitic element can cause interference with circuit operation, thus resulting in a malfunction and then breakdown of the input pin. Therefore, pay thorough attention not to handle the input pins, such as to apply to the input pins a voltage lower than the ground respectively, so that any parasitic element will operate. Furthermore, do not apply a voltage to the input pins when no power supply voltage is applied to the IC. In addition, even if the power supply voltage is applied, apply to the input pins a voltage lower than the guaranteed value of electrical characteristics.

(7) External capacitor

In order to use a ceramic capacitor as the external capacitor, determine the constant with consideration given to a degradation in the nominal capacitance due to DC bias and changes in the capacitance due to temperature, etc.

(8) Thermal shutdown circuit (TSD)

This LSI builds in a thermal shutdown circuit (TSD). When junction temperatures become detection temperature or higher, the thermal shutdown circuit operates and turns a switch OFF. The thermal shutdown circuit, which is aimed at isolating the LSI from thermal runaway as much as possible, is not aimed at the protection or guarantee of the LSI. Therefore, do not continuously use the LSI with this circuit operating or use the LSI assuming its operation.

(9) Thermal design

Perform thermal design in which there are adequate margins by taking into account the permissible dissipation (Pd) in actual states of use. And please care about the Maximum ratings and ASO of the Output's Transistor.

- (10) About the pin for the test, the un-use pin Prevent a problem from being in the pin for the test and the un-use pin under the state of actual use. Please refer to a function manual and an application notebook. And, as for the pin that doesn't specially have an explanation, ask our company person in charge.
- (11) About the rush current

For ICs with more than one power supply, it is possible that rush current may flow instantaneously due to the internal powering sequence and delays. Therefore, give special consideration to power coupling capacitance, width of power wiring, width of ground wiring, and routing of wiring.

(12) About the function description or application note or more

Α

The function description and the application notebook are the design materials to design a set. So, the contents of the materials aren't always guaranteed. Please design application by having fully examination and evaluation include the external elements.

ROHM		PRODUCTS		TYPE	Jisso Inform	nation for	PAGE			
SEMICONDUCTOR Semiconductor					1/4					
SEMICONDUCTOR Semiconductor - Jisso Information - Package : VCSP50L2 (A table of contents) 1. Structure and materials 2. Tape and Reel information 3. Storage conditions 4. Marking lot number 5. Soldering conditions 6. Footprint dimensions 7. External dimensions 8. Precautions					1/4 page 1/4 to 3/4 page 3/4 page 3/4 page 3/4 page 3/4 page 4/4 page 4/4 page					
1. Structure and	mate	erials								
(1)		(5), (6)		No.	Item	Matariala				
				1	Die	Materials Silicon				
				(2)	Cu Post	Cu				
			(2)	3	Mold Compound	Epoxy Resin				
		Q G		4	Ext. terminal	Sn-3Ag-0.5Cu Sol				
				5 (6)	Mold Compound Marking	Polyamide-imide I	Resin			
(3		J			Marking	Laser Marking				
Fig. 1	Stru	cture		Dehydrated weight : 6.3mg						
	Quantity 3,000pcs/Reel					0 0				
2.2.1. Tape and reel dimensions (See the table on page f^{PO} f^{PO} f^{PO} f^{PO} f^{T}					f) Direction of feed of the fe					
DESIGN CHEC	.K	APPROVAL			1					
Hiroyaki Tanigawa K.Kon May, 10, 2011 May, 10	niya	K.Komiya	DATE : May. 1	0,2011	SPECIFICATION N	lo. : TSZ02201-BU26	507GUL-1-2			
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